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ABSTRACT OF THE DISCLOSURE



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SEMICONDUCTOR MEMORY CELL

Provided is a semiconductor memory cell which requires no refreshing operation for retaining information. The semiconductor memory cell comprises a first transistor TR_1 having a first conductivity type, a second transistor TR_2 having a second conductivity type and a MIS type diode DT for retaining information, wherein one source/drain region of the first transistor TR_1 corresponds to the channel forming region CH_2 of the second transistor TR_2 , one source/drain region of the second transistor TR_2 corresponds to the channel forming region CH_1 of the first transistor TR_1 , one end of the MIS type diode DT is formed of an extending portion of the channel forming region CH_1 of the first transistor TR_1 , and the other end of the MIS type diode DT is constituted of an electrode which is formed of an electrically conductive material and connected to a third line having a predetermined potential.

FIGURE 1